

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/524,809
	Filing Date	02/15/2005
	Inventor(s)	James S. Im
	Art Unit	2895
	Examiner Name	Fernando L. Toledo
	Attorney Docket Number	070050.2721

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
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	11.	5620910	4/15/1997	Teramoto, Satoshi
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	15.	6117301	9/12/2000	Freudenberger, Renate ; Zielonka, Andreas
	16.	6198141	3/6/2001	Yamazaki, Shunpei ; Ohtani, Hisashi ; Fukunaga, Takeshi
	17.	6222195	4/24/2001	Yamada, Akio ; Sagou, Satoru ; Watanabe, Hitoshi ; Yamazaki, Satoru ; Sakamoto, Kiichi ; Ohno, Manabu ; Kawakami, Kenichi ; Kobayashi, Katsuhiko
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	19.	6274488	8/14/2001	Talwar, Somit ; Wang, Yun
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	21.	6348990	2/19/2002	Igasaki, Yasunori ; Yoshida, Narihiro ; Toyoda, Haruyoshi ; Hara, Tsutomu
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	49.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti

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	61.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
	62.	6961117	11/1/2005	Im, James S.
	63.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun

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	65.	7217605	5/15/2007	Kawasaki, Ritsuko ; Nakajima, Setsuo
	66.	7259081	8/21/2007	Im, James S.
	67.	7297982	11/20/2007	Suzuki, Kenkichi ; Nagata, Tetsuya ; Takahashi, Michiko ; Saito, Masakazu ; Ogino, Toshio ; Miyano, Masanobu
	68.	7300858	11/27/2007	Im, James S.
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	71.	20020083557	7/4/2002	Jung, Yun Ho
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	80.	20030119286	6/26/2003	Im, James, S. ; Sposili, Robert, S. ; Crowder, Mark, A.
	81.	20030148565	8/7/2003	Yamanaka, Hideo
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	83.	20040127066	7/1/2004	Jung, Yun Ho
	84.	20040140470	7/22/2004	Kawasaki, Ritsuko ; Kasahara, Kenji ; Ohtani, Hisashi
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	86.	20040182838	9/23/2004	Das, Palash, P. ; Bolliger, Bruce, E. ; Patel, Parthiv, S. ; Klene, Brian, C. ; Melcher, Paul, C. ; Saethre, Robert, B.
	87.	20040222187	11/11/2004	Lin, Kun Chih
	88.	20040224487	11/11/2004	Yang, Myoung Su
	89.	20050059265	3/17/2005	Im, James

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	93.	20050202654	9/15/2005	Im, James
	94.	20060030164	2/9/2006	Im, James
	95.	20060102901	5/18/2006	Im, James ; van der Wilt, Paul
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	102.	20070108472	5/17/2007	Jeong, Jae, Kyeong ; Shin, Hyun, Soo ; Kwon, Se, Yeoul ; Mo, Yeon, Gon
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